

# TYPES 1N5226 THRU 1N5257, 1N5226A THRU 1N5257A, 1N5226B THRU 1N5257B SILICON VOLTAGE-REGULATOR DIODES

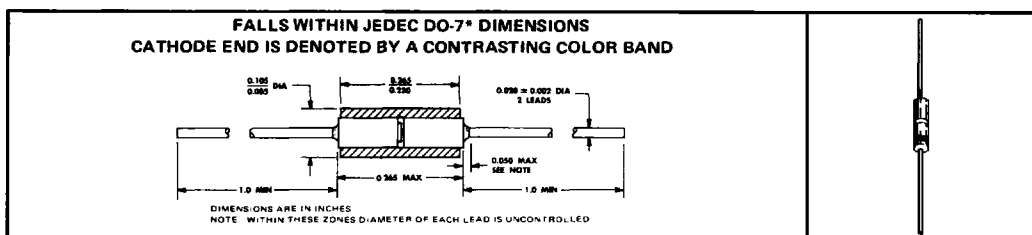
BULLETIN NO. DL-S 7311944, MARCH 1973

$V_Z \dots 3.3 \text{ V to } 33 \text{ V}$   
 $P_D \dots 500 \text{ mW}$

- Available with 5%, 10% and 20% Tolerances
- Rugged Double-Plug Construction

## description and mechanical data

These voltage regulator diodes have been designed using the best of both silicon material processing and packaging technologies. The silicon die is a planar oxide-passivated structure which has additional true-glass passivation over the junction. The double-plug package, proven by years of volume production, ensures the best in mechanical integrity and the lowest possible junction temperature when compared to the thermal characteristics of whisker packages. Because of this rugged double-plug (heat-sink) package, these devices offer very conservatively rated power dissipation capabilities.



## \*absolute maximum ratings at specified lead temperature

Steady-State Regulator Current, $I_{ZM}$ , at (or below) $75^\circ\text{C}$ . . . . .	See Table 2
Continuous Power Dissipation at (or below) $75^\circ\text{C}$ (See Note 1) . . . . .	500 mW
Peak Nonrepetitive Reverse Surge Power at $55^\circ\text{C}$ (See Note 2) . . . . .	10 W
Operating Lead Temperature Range . . . . .	$-65^\circ\text{C}$ to $200^\circ\text{C}$
Lead Temperature 1/16 Inch from Case for 10 Seconds . . . . .	$230^\circ\text{C}$

**TABLE 1—STEADY-STATE REGULATOR CURRENT**

TYPE	$I_{ZM}^\dagger$ (mA)	TYPE	$I_{ZM}^\dagger$ (mA)	TYPE	$I_{ZM}^\dagger$ (mA)	TYPE	$I_{ZM}^\dagger$ (mA)
1N5226, A, B	138	1N5234, A, B	73	1N5242, A, B	38	1N5250, A, B	23
1N5227, A, B	126	1N5235, A, B	67	1N5243, A, B	35	1N5251, A, B	21
1N5228, A, B	115	1N5236, A, B	61	1N5244, A, B	32	1N5252, A, B	19.1
1N5229, A, B	106	1N5237, A, B	55	1N5245, A, B	30	1N5253, A, B	18.2
1N5230, A, B	97	1N5238, A, B	52	1N5246, A, B	28	1N5254, A, B	16.8
1N5231, A, B	89	1N5239, A, B	50	1N5247, A, B	27	1N5255, A, B	16.2
1N5232, A, B	81	1N5240, A, B	45	1N5248, A, B	25	1N5256, A, B	15.1
1N5233, A, B	76	1N5241, A, B	41	1N5249, A, B	24	1N5257, A, B	13.8

$^\dagger$ The nominal  $I_{ZM}$  currents shown are applicable for devices having regulator voltages approximately 10% above the nominal  $V_Z$  values shown under electrical characteristics. These values do not represent absolute limits. The actual steady-state current-voltage product must not exceed the power rating.

- NOTES: 1. Derate linearly to  $200^\circ\text{C}$  lead temperature at the rate of  $4 \text{ mW}/^\circ\text{C}$ .  
2. This value applies for an 8.3-ms square-wave pulse with the device at nonoperating thermal equilibrium immediately prior to the surge.

\*JEDEC registered data. This data sheet contains all applicable registered data in effect at the time of publication.

10

**TYPES 1N5226 THRU 1N5257,  
1N5226A THRU 1N5257A, 1N5226B THRU 1N5257B  
SILICON VOLTAGE-REGULATOR DIODES**

**1N5226 THRU 1N5257**

\*electrical characteristics at 25°C lead temperature

CHARACTERISTICS					
PARAMETER	V <sub>Z</sub> Regulator Voltage	I <sub>R</sub> Static Reverse Current	V <sub>F</sub> Static Forward Voltage	TEST CURRENT AND VOLTAGE	
				I <sub>Z</sub> (T)	V <sub>R</sub> (T)
TEST CONDITIONS	I <sub>R</sub> = I <sub>Z</sub> (T), See Note 3	V <sub>R</sub> = V <sub>R</sub> (T)	I <sub>F</sub> = 200 mA		
LIMIT	NOM <sup>‡</sup>	MAX	MAX		
UNIT	V	μA	V	mA	V
1N5226	3.3	100	1.1	20	0.95
1N5227	3.6	100	1.1	20	0.95
1N5228	3.9	75	1.1	20	0.95
1N5229	4.3	50	1.1	20	0.95
1N5230	4.7	50	1.1	20	1.9
1N5231	5.1	50	1.1	20	1.9
1N5232	5.6	50	1.1	20	2.9
1N5233	6.0	50	1.1	20	3.3
1N5234	6.2	50	1.1	20	3.8
1N5235	6.8	30	1.1	20	4.8
1N5236	7.5	30	1.1	20	5.7
1N5237	8.2	30	1.1	20	6.2
1N5238	8.7	30	1.1	20	6.2
1N5239	9.1	30	1.1	20	6.7
1N5240	10	30	1.1	20	7.6
1N5241	11	30	1.1	20	8.0
1N5242	12	10	1.1	20	8.7
1N5243	13	10	1.1	9.5	9.4
1N5244	14	10	1.1	9.0	9.5
1N5245	15	10	1.1	8.5	10.5
1N5246	16	10	1.1	7.8	11.4
1N5247	17	10	1.1	7.4	12.4
1N5248	18	10	1.1	7.0	13.3
1N5249	19	10	1.1	6.6	13.3
1N5250	20	10	1.1	6.2	14.3
1N5251	22	10	1.1	5.6	16.2
1N5252	24	10	1.1	5.2	17.1
1N5253	25	10	1.1	5.0	18.1
1N5254	27	10	1.1	4.6	20
1N5255	28	10	1.1	4.5	20
1N5256	30	10	1.1	4.2	22
1N5257	33	10	1.1	3.8	24

<sup>‡</sup>V<sub>Z</sub> tolerance is ±20% for 1N5226 thru 1N5257. See next page for 5%-tolerance and 10%-tolerance devices.

NOTE 3: V<sub>Z</sub> is measured with the device at thermal equilibrium while held in clips at least 3/8 inch from the case in still air at 25°C.

\*JEDEC registered data

# TYPES 1N5226 THRU 1N5257, 1N5226A THRU 1N5257A, 1N5226B THRU 1N5257B SILICON VOLTAGE-REGULATOR DIODES

## 1N5226A THRU 1N5257A AND 1N5226B THRU 1N5257B

\*electrical characteristics at 25°C lead temperature (unless otherwise noted)

CHARACTERISTICS							TEST CURRENT AND VOLTAGE		
PARAMETER	V <sub>Z</sub> Regulator Voltage	αV <sub>Z</sub> Temperature Coefficient of Regulator Voltage	z <sub>Z</sub> Small-Signal Regulator Impedance	z <sub>ZK</sub> Small-Signal Regulator Knee Impedance	I <sub>R</sub> Static Reverse Current	V <sub>F</sub> Static Forward Voltage			
TEST CONDITIONS	I <sub>R</sub> = I <sub>Z</sub> (T), See Note 3	See Note 4	I <sub>R</sub> = I <sub>Z</sub> (T), I <sub>F</sub> = 10% I <sub>Z</sub> (T), f = 60 Hz	I <sub>ZK</sub> = 250 μA, I <sub>ZK</sub> = 25 μA, f = 60 Hz	V <sub>R</sub> = V <sub>R</sub> (T)	I <sub>F</sub> = 200 mA	I <sub>Z</sub> (T)	1N5226A thru 1N5257A	1N5226B thru 1N5257B
LIMIT	NOM <sup>§</sup>	MAX	MAX	MAX	MAX	MAX			
UNIT	V	%/°C	Ω	Ω	μA	V	mA	V	V
1N5226A, B	3.3	-0.070	28	1600	25	1.1	20	0.95	1.0
1N5227A, B	3.6	-0.065	24	1700	15	1.1	20	0.95	1.0
1N5228A, B	3.9	-0.060	23	1900	10	1.1	20	0.95	1.0
1N5229A, B	4.3	±0.055	22	2000	5	1.1	20	0.95	1.0
1N5230A, B	4.7	±0.030	19	1900	5	1.1	20	1.9	2.0
1N5231A, B	5.1	±0.030	17	1600	5	1.1	20	1.9	2.0
1N5232A, B	5.6	+0.038	11	1600	5	1.1	20	2.9	3.0
1N5233A, B	6.0	+0.038	7	1600	5	1.1	20	3.3	3.5
1N5234A, B	6.2	+0.045	7	1000	5	1.1	20	3.8	4.0
1N5235A, B	6.8	+0.050	5	750	3	1.1	20	4.8	5.0
1N5236A, B	7.5	+0.058	6	500	3	1.1	20	5.7	6.0
1N5237A, B	8.2	+0.062	8	500	3	1.1	20	6.2	6.5
1N5238A, B	8.7	+0.065	8	600	3	1.1	20	6.2	6.5
1N5239A, B	9.1	+0.068	10	600	3	1.1	20	6.7	7.0
1N5240A, B	10	+0.075	17	600	3	1.1	20	7.6	8.0
1N5241A, B	11	+0.076	22	600	2	1.1	20	8.0	8.4
1N5242A, B	12	+0.077	30	600	1	1.1	20	8.7	9.1
1N5243A, B	13	+0.079	13	600	0.5	1.1	9.5	9.4	9.9
1N5244A, B	14	+0.082	15	600	0.1	1.1	9.0	9.5	10
1N5245A, B	15	+0.082	16	600	0.1	1.1	8.5	10.5	11
1N5246A, B	16	+0.083	17	600	0.1	1.1	7.8	11.4	12
1N5247A, B	17	+0.084	19	600	0.1	1.1	7.4	12.4	13
1N5248A, B	18	+0.085	21	600	0.1	1.1	7.0	13.3	14
1N5249A, B	19	+0.086	23	600	0.1	1.1	6.6	13.3	14
1N5250A, B	20	+0.086	25	600	0.1	1.1	6.2	14.3	15
1N5251A, B	22	+0.087	29	600	0.1	1.1	5.6	16.2	17
1N5252A, B	24	+0.088	33	600	0.1	1.1	5.2	17.1	18
1N5253A, B	25	+0.089	35	600	0.1	1.1	5.0	18.1	19
1N5254A, B	27	+0.090	41	600	0.1	1.1	4.6	20	21
1N5255A, B	28	+0.091	44	600	0.1	1.1	4.5	20	21
1N5226A, B	30	+0.091	49	600	0.1	1.1	4.2	22	23
1N5257A, B	33	+0.092	58	700	0.1	1.1	3.8	24	25

§ V<sub>Z</sub> tolerance is ±10% for 1N5226A thru 1N5257A series; ±5% for 1N5226B thru 1N5257B series. See preceding page for 20%-tolerance devices.

NOTES: 3. V<sub>Z</sub> is measured with the device at thermal equilibrium while held in clips at least 3/8 inch from the case in still air at 25°C.

$$4. \text{ Temperature Coefficient } \alpha V_Z = \frac{[V_Z @ 125^\circ\text{C}] - [V_Z @ 25^\circ\text{C}]}{V_Z @ 25^\circ\text{C}} \times \frac{100\%}{125^\circ\text{C} - 25^\circ\text{C}}$$

For determining αV<sub>Z</sub>, V<sub>Z</sub> is measured at 7.5 mA for 1N5226A/1N5226B thru 1N5242A/1N5242B and at I<sub>ZT</sub> for 1N5243A/1N5243B thru 1N5257A/1N5257B.

\*JEDEC registered data

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373